



Vishay High Power Products

# Power Silicon Rectifier Diodes, 35 A/40 A/60 A

# 35 A/40 A/60 A



DO-203AB (DO-5)

35 A/40 A/60 A

#### **DESCRIPTION/FEATURES**



- Good surge current capability up to 1000 A
- Can be supplied to meet stringent military, aerospace and other high reliability requirements
- Compliant to RoHS directive 2002/95/EC

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	1N1183	1N3765	1N1183A	1N2128A	UNITS	
1		35 <sup>(1)</sup>	35 (1)	40 (1)	60 <sup>(1)</sup>	Α	
I <sub>F(AV)</sub>	T <sub>C</sub>	140 (1)	140 (1)	150 <sup>(1)</sup>	140 <sup>(1)</sup>	°C	
I <sub>FSM</sub>	50 Hz	480	380	765	860	۸	
	60 Hz	500 <sup>(1)</sup>	400 (1)	800 (1)	900 (1)	Α	
l <sup>2</sup> t	50 Hz	1140	730	2900	3700	A <sup>2</sup> s	
	60 Hz	1040	670	2650	3400	A-S	
I <sup>2</sup> √t		16 100	10 300	41 000	52 500	A²√s	
$V_{RRM}$	Range	50 to 600 <sup>(1)</sup>	700 to 1000 <sup>(1)</sup>	50 to 600 <sup>(1)</sup>	50 to 600 <sup>(1)</sup>	V	

#### Note

**PRODUCT SUMMARY** 

I<sub>F(AV)</sub>

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS						
TYPE NUMBER		$V_{RRM}$ , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE $(T_J = -65  ^{\circ}\text{C TO } 200  ^{\circ}\text{C }^{(2)})$ V	$V_{RM}$ , MAXIMUM DIRECT REVERSE VOLTAGE ( $T_J = -65~^{\circ}C$ TO 200 $^{\circ}C$ $^{(2)}$ ) V			
1N1183	1N1183A	1N2128A	50 <sup>(1)</sup>	50 <sup>(1)</sup>		
1N1184	1N1184A	1N2129A	100 (1)	100 (1)		
1N1185	1N1185A	1N2130A	150 <sup>(1)</sup>	150 <sup>(1)</sup>		
1N1186	1N1186A	1N2131A	200 (1)	200 (1)		
1N1187	1N1187A	1N2133A	300 (1)	300 (1)		
1N1188	1N1188A	1N2135A	400 (1)	400 (1)		
1N1189	1N1189A	1N2137A	500 <sup>(1)</sup>	500 <sup>(1)</sup>		
1N1190	1N1190A	1N2138A	600 <sup>(1)</sup>	600 <sup>(1)</sup>		
1N3765			700 (1)	700 (1)		
1N3766			800 (1)	800 (1)		
1N3767			900 (1)	900 (1)		
1N3768			1000 (1)	1000 (1)		

#### Notes

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<sup>(1)</sup> JEDEC registered values

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 $<sup>^{(2)}</sup>$  For 1N1183 Series and 1N3765 Series  $T_C$  = - 65  $^{\circ}C$  to 190  $^{\circ}C$ 

<sup>•</sup> Basic type number indicates cathode to case. For anode to case, add "R" to part number, e.g., 1N1188R, 1N3766R, 1N1186AR, 1N2135AR



### Power Silicon Rectifier Diodes, 35 A/40 A/60 A



PARAMETER	SYMBOL	TEST CONDITIONS		1N1183	1N3765	1N1183A	1N2128A	UNITS
Maximum average forward current	I <sub>F(AV)</sub>	1-phase operation, 180° sinusoidal conduction		35 <sup>(1)</sup>	35 <sup>(1)</sup>	40 (1)	60 (1)	Α
at case temperature				140 (1)	140 <sup>(1)</sup>	150 <sup>(1)</sup>	140 <sup>(1)</sup>	°C
		Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with rated V <sub>RRM</sub> applied	480	380	765	860	А
Maximum peak one cycle		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		500 <sup>(1)</sup>	400 (1)	800 (1)	900 (1)	
non-repetitive surge current	I <sub>FSM</sub>	Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with ½ V <sub>RRM</sub> applied following surge = 0	570	455	910	1000	
		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		595	475	950	1050	
Mandan 124 fau f	- l <sup>2</sup> t	t = 10 ms	With rated $V_{RRM}$ applied following surge, initial $T_J = T_J$ maximum	1140	730	2900	3700	A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing		t = 8.3 ms		1040	670	2650	3400	
Maximum I <sup>2</sup> t for individual		t = 10 ms	With $V_{RRM} = 0$ following surge, initial $T_J = T_J$ maximum	1610	1030	4150	5250	
device fusing		t = 8.3 ms		1470	940	3750	4750	
Maximum l²√t for individual device fusing	2√t (2)	t = 0.1 to 10 ms, V <sub>RRM</sub> = 0 following surge		16 100	10 300	41 500	52 500	A²√s
Maximum peak forward voltage	V	T <sub>J</sub> = 25 °C		1.7 (1)	1.8 (1)	1.3 (1)	1.3 <sup>(1)</sup>	V
at maximum forward current (I <sub>FM</sub> )	$V_{FM}$			110	110	126	188	Α
V <sub>RRM</sub> = 700				-	5.0 <sup>(1)</sup>	-	-	
V <sub>RRM</sub> = 800		Mandania	$_{AV)}$ and $T_{C}$	-	4.0 (1)	-	-	mA
Maximum average reverse current $V_{RRM} = 900$	I <sub>R(AV)</sub>	Maximum rated I <sub>F(</sub> ,		-	3.0 (1)	-	-	
V <sub>RRM</sub> = 1000				-	2.0 (1)	-	-	
		Maximum rated I <sub>F(AV)</sub> , V <sub>RRM</sub> and T <sub>C</sub>		10 <sup>(1)</sup>	-	2.5 <sup>(1)</sup>	10 <sup>(1)</sup>	

#### Notes

Document Number: 93492 Revision: 25-May-09

<sup>(1)</sup> JEDEC registered values

<sup>(2)</sup> I<sup>2</sup>t for time  $t_x = I^2 \sqrt{t} \times \sqrt{t_x}$ 



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THERMAL AND MEC	1				l		1
PARAMETER	SYMBOL	TEST CONDITIONS		1N3765	1N1183A	1N2128A	UNITS
Maximum operating case temperature range	T <sub>C</sub>		- 65 to 190 <sup>(1)</sup>		- 65 to 200		- °C
Maximum storage temperature range	T <sub>Stg</sub>		- 65 to	- 65 to 175 <sup>(1)</sup>		- 65 to 200	
Maximum internal thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.00 (1)		1.1 <sup>(1)</sup>	0.65 (1)	· °C/W
Thermal resistance, case to sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.25			C/VV	
		Not lubricated thread, tighting on nut (2)	3.4 (30)				N ⋅ m (lbf ⋅ in)
Maximum allowable		Lubricated thread, tighting on nut (2)			2.3 (20)		
mounting torque (+ 0 %, - 10 %)		Not lubricated thread, tighting on hexagon (3)	4.2 (37)				
		Lubricated thread, tighting on hexagon (3)	3.2 (28)				
Approximate weight			17 0.6			g	
Approximate weight					OZ.		
Case style		JEDEC	DO-203AB (DO-5)				•

#### **Notes**

- (1) JEDEC registered values
- (2) Recommended for pass-through holes
  (3) Recommended for holed threaded heatsinks

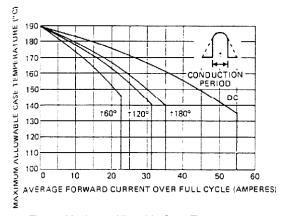


Fig. 1 - Maximum Allowable Case Temperature vs. Average Forward Current, 1N1183 and 1N3765 Series

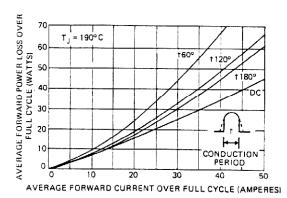


Fig. 2 - Typical Low Level Forward Power Loss vs. Average Forward Current (Sinusoidal Current Waveform), 1N1183 and 1N3765 Series

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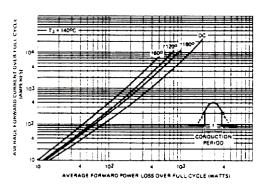


Fig. 3 - Typical High Level Forward Power Loss vs. Average Forward Current (Sinusoidal Current Waveform), 1N1183 and 1N3765 Series

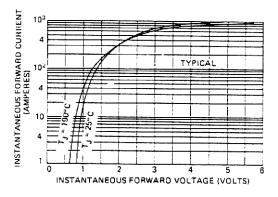


Fig. 4 - Typical Forward Voltage vs. Forward Current, 1N1183 and 1N3765 Series

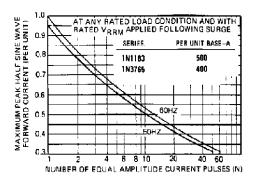


Fig. 5 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 1N1183 and 1N3765 Series

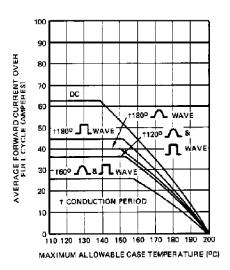


Fig. 6 - Average Forward Current vs. Maximum Allowable Case Temperature, 1N1183A Series

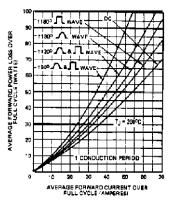


Fig. 7 - Maximum Low Level Forward Power Loss vs. Average Forward Current, 1N1183A Series

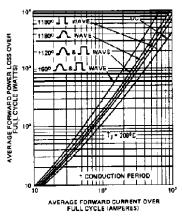


Fig. 8 - Maximum High Level Forward Power Loss vs. Average Forward Current, 1N1183A Series



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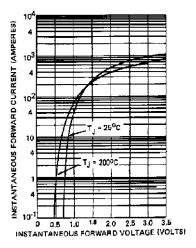


Fig. 9 - Maximum Forward Voltage vs. Forward Current, 1N1183A Series

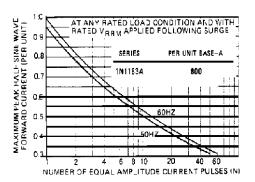


Fig. 10 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 1N1183A Series

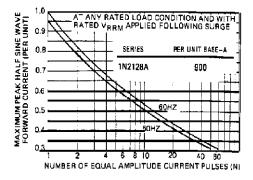


Fig. 11 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 1N2128A Series

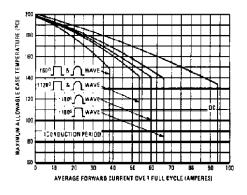


Fig. 12 - Maximum Allowable Case Temperature vs. Average Forward Current, 1N2128A Series

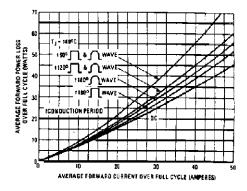


Fig. 13 - Maximum Low Level Forward Power Loss vs. Average Forward Current, 1N2128A Series

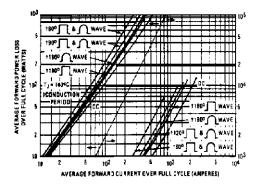


Fig. 14 - Maximum High Level Forward Power Loss vs. Average Forward Current, 1N2128A Series

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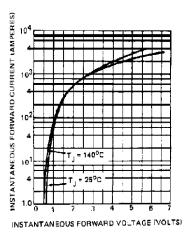


Fig. 15 - Maximum Forward Voltage vs. Forward Current, 1N2128A Series

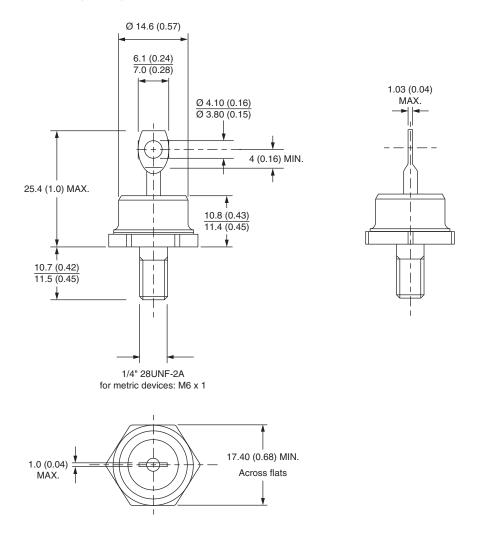
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95360			



Vishay Semiconductors

## DO-203AB (DO-5) for 1N1183, 1N3765, 1N1183A, 1N2128A, 1N3208 Series

**DIMENSIONS** in millimeters (inches)





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